

HF Bipolar Transistors (continued)

S	BFR 93 A	23932	NPN	35	12	300	6	1,6-2,1	SOT-23(+R2)
S	BFR 96 TS	30148	NPN	100	15	700	5	3,3-4	SOT 37

IGBT Modules

The insulated gate bipolar transistor or IGBT is a three-terminal power semiconductor device, noted for high efficiency and fast switching. It switches electric power in many modern appliances: electric cars, variable speed refrigerators, air-conditioners and even stereo systems with switching amplifiers. The IGBT combines the simple gate-drive characteristics of the MOSFETs with the high-current and low-saturation-voltage capability of bipolar transistors by combining an isolated gate FET for the control input, and a bipolar power transistor as a switch, in a single device. The IGBT is used in medium- to high-power applications such as switched-mode power supply, traction motor control and induction heating.

Part No.	Ord.No.	Uds[V]	Id[mA]	Ptot[W]	Housing
S BUP 212	34193	1200	22	125	TO-220
S BUP 313	34196	1200	32	200	TO-218
S BUP 314	40135	1200	52	300	TO-218

Housing dimensions can be found in the back of the catalogue..

Low-Power Field-Effect Transistors (Small Signal MOSFETs)

Part No.	Ord.No.	Polarity	Uds[V]	Id[mA]	Ptot[W]	Rdson[Ω]	Housing
S BF 245 A	13876	JFET-N	30	25	300	$I_{DSS}=6,5mA$	TO-92 GSD*
S BF 245 B	13877	JFET-N	30	25	300	$I_{DSS}=15mA$	TO-92 GSD*
S BF 245 C	13878	JFET-N	30	25	300	$I_{DSS}=25mA$	TO-92 GSD*
O BF 998	29462	BIFET N	12	30	-	-	SOT-143
S BS 107	13943	VMOS-N	200	250	350	14R	TO-92 GSD*
S BS 107 BULK	73149	VMOS-N	200	150		14R	TO-92
S BS 108	36403	VMOS-N	200	250	1000	8R	TO-92 GSD*
S BS 170	13944	VMOS-N	60	500	830	5R	TO-92 GSD*
S BS 170 BULK	73151	VMOS-N	60			5R	TO-92
S BS 250	13945	VMOS-P	-45	-250	830	14R	TO-92 GSD*
S BSN 20	36393	MOSFET-N	50	100	250	15R	SOT-23
S BSS 123	32794	MOSFET-N	100	170	300	6R	SOT-23
S BSS 138	34802	MOSFET-N	50	200	360	3,5R	SOT-23
S BSS 83 P	8231	MOSFET-P	-60	-330	360	2R	SOT-23
S BSS 84	32792	MOSFET-P	-50	-130	360	10R	SOT-23

Power Field-Effect Transistors (Power MOSFETs)

Part No.	Ord.No.	Polarity	Uds [V]	Id[A]	Ptot[W]	Rdson[Ω]	Housing
S BSP250	40273	FET P	-30	-3	5	0,25	SOT 223
S BUZ11	22440	FET N	50	30	75	0,04	TO 220
S BUZ71A	20501	FET N	55	16	70	0,12	TO 220
S BUZ80A	32787	FET N	800	3	75	3	TO 220
S BUZ90	24156	FET N	600	6	75	1,6	TO 220
O FDS6875	48213	FET 2xP	-20	-6	2	0,03	SO 8
S IRF1010N	3743	FET N	55	84	170	0,011	TO 220
O IRF1405	47260	FET N	55	169	330	0,0053	TO 220
O IRF2807S	46572	FET N	75	82	200	0,013	D2PAK
S IRF3205	6961	FET N	55	110	200	0,008	TO 220
S IRF3710	6986	FET N	100	57		0,023	TO 220
S IRF4905	11728	FET P	-55	-74	200	0,02	TO 220
S IRF510	2487	FET N	100	5,6	43	0,4	TO 220
S IRF520	22445	FET N	100	9,2	60	0,27	TO 220
S IRF530	22446	FET N	100	16	90	0,16	TO 220
S IRF530N	71967	FET N	100	17	70	0,9	TO 220
S IRF540	22447	FET N	100	28	150	0,077	TO 220
S IRF540N	4335	FET N	100	33	130	0,044	TO 220
S IRF630	40819	FET N	200	9	74	0,4	TO 220
S IRF640	32783	FET N	200	18	125	0,18	TO 220
S IRF640N	67650	FET N	18	200	150	0,15	TO 220
O IRF710	45942	FET N	400	2	36	3,6	TO 220
S IRF730	32784	FET N	400	5,5	100	1	TO 220
S IRF7301	47592	FET 2XN	20	5,2	2	0,05	SO8
S IRF7314	55477	FET 2XP	-20	-5,3		0,058	SO8
S IRF7341	9597	FET 2XN	55	4,7	2	0,05	SO 8
S IRF7342	9596	FET 2xP	-55	-3,4	2	0,105	SO 8
S IRF7343	9595	FET N+P	55	+4,7/-3,4	2	0,05/0,105	SO 8
S IRF740	22457	FET N	+/-400	10	125	0,55	TO 220
O IRF7450	9594	FET N	200	2,5	2,5	0,17	SO 8
S IRF 820	22458	FET N	500	2,5	50	3,0	TO 220
S IRF 830	22459	FET N	500	4,5	100	1,5	TO 220

SO-8



SOT-143



SOT-23



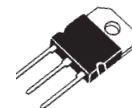
SOT-223



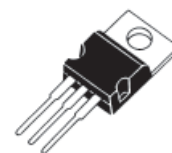
SOT-47



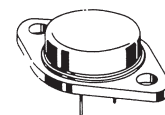
TO 218



TO-220



TO3



TO92

